



CYPRESS

CY54/74FCT399T

Quad 2-Input Register

Features

- Function, pinout and drive compatible with FCT and F logic
- FCT-C speed at 6.1 ns max. (Com'I)
FCT-A speed at 7.0 ns max. (Com'I)
- Reduced V_{OH} (typically = 3.3V)
versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- Power-off disable feature
- Matched rise and fall times

- ESD > 2000V

- Fully compatible with TTL input and output logic levels

- Sink current 64 mA (Com'I),
32 mA (Mil)
- Source current 32 mA (Com'I),
12 mA (Mil)

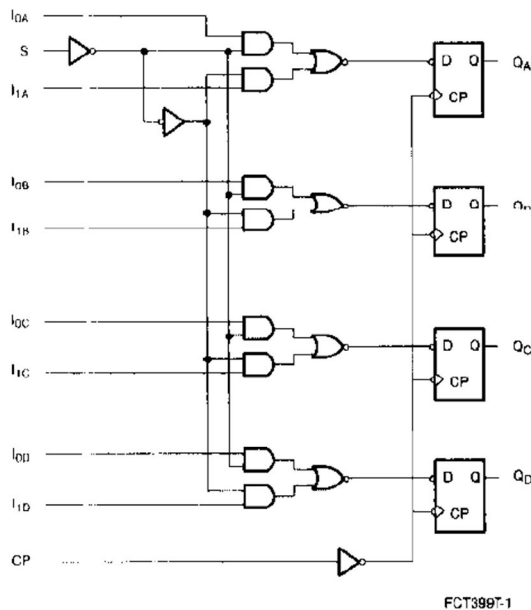
Functional Description

The FCT399T is a high-speed quad dual-port register that selects four bits of data from either of two sources (Ports) under control of a common Select input

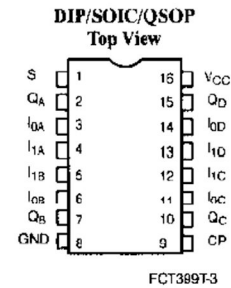
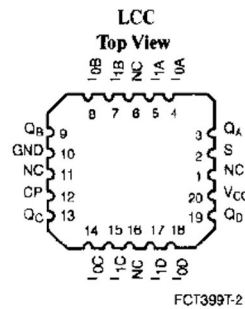
(S). The selected data is transferred to a 4-bit output register synchronous with the LOW-to-HIGH transition of the Clock input (CP). The 4-bit D-type output register is fully edge-triggered. The Data inputs (I_{0X} , I_{1X}) and Select input (S) must be stable only one set-up time prior to, and hold time after, the LOW-to-HIGH transition of the Clock input for predictable operation. The FCT399T offers true outputs.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.

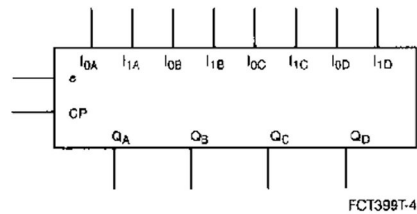
Logic Block Diagram



Pin Configurations



Logic Symbol



Pin Description

Name	Description
S	Common Select Input
CP	Clock Pulse Input (Active Rising Edge)
I_0	Data Inputs from Source 0
I_1	Data Inputs from Source 1
Q	Register True Outputs

Function Table^[1]

Inputs			Outputs
S	I_0	I_1	Q
l	l	X	L
h	h	X	H
h	X	l	L
h	X	h	H

Note:

- 1. H = HIGH Voltage Level
- h = HIGH Voltage Level one set-up time prior to the LOW-to-HIGH Clock Transition
- L = LOW Voltage Level
- l = LOW Voltage Level one set-up time prior to the LOW-to-HIGH Clock Transition
- X = Don't Care



Maximum Ratings^[2, 3]

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	−65°C to +150°C
Ambient Temperature with Power Applied	−65°C to +135°C
Supply Voltage to Ground Potential	−0.5V to +7.0V
DC Input Voltage	−0.5V to +7.0V
DC Output Voltage	0.5V to +7.0V
DC Output Current (Maximum Sink Current/Pin)	120 mA
Power Dissipation	0.5W

Static Discharge Voltage >2001 V
(per MIL-STD-883, Method 3015)

Operating Range

Range	Range	Ambient Temperature	V _{CC}
Commercial	CT	0°C to +70°C	5V ± 5%
Commercial	T, AT	40°C to +85°C	5V ± 5%
Military ^[4]	All	−55°C to +125°C	5V ± 10%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	Min.	Typ. ^[5]	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = −32 mA, Com'l	2.0			V
		V _{CC} = Min., I _{OH} = −15 mA, Com'l	2.4	3.3		V
		V _{CC} = Min., I _{OH} = −12 mA, Mil	2.4	3.3		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 64 mA, Com'l		0.3	0.55	V
		V _{CC} = Min., I _{OL} = 32 mA, Mil		0.3	0.55	V
V _{IH}	Input HIGH Voltage		2.0			V
V _{IL}	Input LOW Voltage				0.8	V
V _{HT}	Hysteresis ^[6]	All inputs		0.2		V
V _{IK}	Input Clamp Diode Voltage	V _{CC} = Min., I _{IN} = −18 mA		−0.7	−1.2	V
I _I	Input HIGH Current	V _{CC} = Max., V _{IN} = V _{CC}			5	μA
I _{IH}	Input HIGH Current	V _{CC} = Max., V _{IN} = 2.7V			±1	μA
I _{IL}	Input LOW Current	V _{CC} = Max., V _{IN} = 0.5V			±1	μA
I _{OS}	Output Short Circuit Current ^[7]	V _{CC} = Max., V _{OUT} = 0.0V	−60	−120	−225	mA
I _{ON}	Power-Off Disable	V _{CT} = 0V, V _{OUT} = 4.5V			±1	μA

Capacitance^[6]

Parameter	Description	Typ. ^[5]	Max.	Unit
C _{IN}	Input Capacitance	5	10	pF
C _{OUT}	Output Capacitance	9	12	pF

Notes:

- Unless otherwise noted, these limits are over the operating free-air temperature range.
- Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CT} or ground.
- T_A is the "instant on" case temperature.
- Typical values are at V_{CT} = 5.0V, T_A = +25°C ambient.
- This parameter is guaranteed but not tested.
- Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques is preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
I_{CC}	Quiescent Power Supply Current	$V_{CC} = \text{Max.}, V_{IN} \leq 0.2V,$ $V_{IN} \geq V_{CC} - 0.2V$	0.1	0.2	mA
ΔI_{CC}	Quiescent Power Supply Current (TTL inputs)	$V_{CC} = \text{Max.}, V_{IN} = 3.4V^{[8]}$ $f_I = 0, \text{Outputs Open}$	0.5	2.0	mA
I_{CCD}	Dynamic Power Supply Current ^[9]	$V_{CC} = \text{Max.}, \text{One Input Toggling},$ 50% Duty Cycle, Outputs Open, $V_{IN} \leq 0.2V \text{ or } V_{IN} \geq V_{CC} - 0.2V$	0.06	0.12	mA/ MHz
I_C	Total Power Supply Current ^[10]	$V_{CC} = \text{Max.}, f_0 = 10 \text{ MHz},$ 50% Duty Cycle, Outputs Open, One Input Toggling at $f_I = 5 \text{ MHz},$ S=Steady State $V_{IN} \leq 0.2V \text{ or } V_{IN} \geq V_{CC} - 0.2V$	0.7	1.4	mA
		$V_{CC} = \text{Max.}, f_0 = 10 \text{ MHz},$ 50% Duty Cycle, Outputs Open, One Input Toggling at $f_I = 5 \text{ MHz},$ S=Steady State $V_{IN} = 3.4V \text{ or } V_{IN} = \text{GND}$	1.2	3.4	mA
		$V_{CC} = \text{Max.}, f_0 = 10 \text{ MHz},$ 50% Duty Cycle, Outputs Open, Four Inputs Toggling at $f_I = 5 \text{ MHz},$ S=Steady State $V_{IN} \leq 0.2V \text{ or } V_{IN} \geq V_{CC} - 0.2V$	1.6	3.2 ^[11]	mA
		$V_{CC} = \text{Max.}, f_0 = 10 \text{ MHz},$ 50% Duty Cycle, Outputs Open, Four Inputs Toggling at $f_I = 5 \text{ MHz},$ S=Steady State $V_{IN} = 3.4V \text{ or } V_{IN} = \text{GND}$	2.9	8.2 ^[11]	mA

Notes:

8. Per TTL driven input ($V_{IN} = 3.4V$); all other inputs at V_{CC} or GND.

9. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

10. $I_C = I_{\text{QUIESCENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$

$I_C = I_{CC} + \Delta I_{CC} D_{HI} N_I + I_{CCD} (f_0/2 + f_I N_I)$

I_{CC} = Quiescent Current with CMOS input levels

ΔI_{CC} = Power Supply Current for a TTL HIGH input

($V_{IN} = 3.4V$)

D_{HI} = Duty Cycle for TTL inputs HIGH

N_I = Number of TTL inputs at D_{HI}

I_{CCD} = Dynamic Current caused by an input transition pair (HLH or LHL)

f_0 = Clock frequency for registered devices, otherwise zero

f_I = Input signal frequency

N_I = Number of inputs changing at f_I

All currents are in milliamps and all frequencies are in megahertz.

11. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

Switching Characteristics Over the Operating Range

Parameter	Description	FCT399T				FCT399AT				Unit	Fig. No. ^[13]
		Military		Commercial		Military		Commercial			
		Min. ^[12]	Max.	Min. ^[12]	Max.	Min. ^[12]	Max.	Min. ^[12]	Max.		
t _{PLH} t _{PHL}	Propagation Delay CP to Q	3.0	11.5	3.0	10.0	2.5	7.5	2.5	7.0	ns	1, 5
t _S	Set-Up Time HIGH or LOW I _n to CP	4.5		3.5		4.0		3.5		ns	4
t _H	Hold Time HIGH or LOW I _n to CP	1.5		1.0		1.0		1.0		ns	4
t _S	Set-Up Time HIGH or LOW S to CP	9.5		8.5		9.0		8.5		ns	4
t _H	Hold Time HIGH or LOW S to CP	0		0		0		0		ns	4
t _w	Clock Pulse Width ^[6] HIGH or LOW	7.0		5.0		6.0		5.0		ns	5

Parameter	Description	FCT399CT				Unit	Fig. No. ^[13]
		Military		Commercial			
		Min. ^[12]	Max.	Min. ^[12]	Max.		
t _{PLH} t _{PHL}	Propagation Delay CP to Q	2.5	6.6	2.5	6.1	ns	1, 5
t _S	Set-Up Time, HIGH or LOW, I _n to CP	4.0		3.5		ns	4
t _H	Hold Time, HIGH or LOW, I _n to CP	1.0		1.0		ns	4
t _S	Set-Up Time, HIGH or LOW, S to CP	9.0		8.5		ns	4
t _H	Hold Time, HIGH or LOW, S to CP	0		0		ns	4
t _w	Clock Pulse Width ^[6] HIGH or LOW	6.0		5.0		ns	5

Notes:

12. Minimum limits are guaranteed but not tested on Propagation Delays.

13. See "Parameter Measurement Information" in the General Information Section.

**Ordering Information**

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
6.1	CY74FCT399CTPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT399CTQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT399CTSOC	S1	16-Lead (300-Mil) Molded SOIC	
6.6	CY54FCT399CTDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT399CTLMB	L61	20-Pin Square Leadless Chip Carrier	
7.0	CY74FCT399ATPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT399ATQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT399ATSOC	S1	16-Lead (300-Mil) Molded SOIC	
7.5	CY54FCT399ATDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT399ATLMB	L61	20-Pin Square Leadless Chip Carrier	
10.0	CY74FCT399TPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT399TQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT399TSOC	S1	16-Lead (300-Mil) Molded SOIC	
11.5	CY54FCT399TDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT399TLMB	L61	20-Pin Square Leadless Chip Carrier	